

★ Under development

### ■ 5 V/12 V Dual-Power-Supply Flash Memories

Capacity	Configuration (words x bits)	Erase block size (bytes)	Model No.	Access time (ns) MAX.	Supply voltage	Read current (mA) MAX. (f=8MHz)	Standby current ( $\mu$ A) MAX.	Operating temp. ( $^{\circ}$ C)	Package			
8M	1M x 8	64k	LH28F008SAT/R/N-85	85	Vcc = 5 V	50	100	0 to 70	40TSOP(I) Normal / Reverse / 44SOP			
			LH28F008SAT/R/N-12	120	Vpp = 12 V							
			★LH28F008SAT/R/B-KF85	85	Vcc = 5 V	50	100	0 to 70		40TSOP(I) Normal / Reverse / 42FBGA(CSP)		
			★LH28F008SAT/R/B-KF12	120	Vpp = 12 V							
			LH28F008SAHT/R/N-85	85	Vcc = 5 V	50	100	-40 to 85			40TSOP(I) Normal / Reverse / 44SOP	
			LH28F008SAHT/R/N-12	120	Vpp = 12 V							
			★LH28F008SAHT/R/B-KF85	85	Vcc = 5 V	50	100	-25 to 85				40TSOP(I) Normal / Reverse / 42FBGA(CSP)
			★LH28F008SAHT/R/B-KF12	120	Vpp = 12 V							
16M	2M x 8 1M x 16	64k	LH28F016SAT/R-70	70(120*1)	Vcc = 5 V (3.3 V read available)	60(35*1)	100	0 to 70	56TSOP(I) Normal / Reverse			
			LH28F016SAT/R-10	100(150*1)	Vpp = 12 V							

### ■ 3 V/5 V Dual-Power-Supply Flash Memories

Capacity	Configuration (words x bits)	Erase block size (bytes)	Model No.	Access time (ns) MAX.	Supply voltage	Read current (mA) MAX. (f=10MHz)	Standby current ( $\mu$ A) MAX.	Operating temp. ( $^{\circ}$ C)	Package	
2M	256k x 8	16k	LH28F020SUT/N-L12	120	Vcc = 3.3 V (2.7 V read available)	35	80	0 to 70	32TSOP(I) Normal / 32SOP	
			LH28F020SUT/N-L15	150	Vpp = 5 V					
			★LH28F020SUHT/N-L12	120	Vcc = 3.3 V (2.7 V read available)	35	80	-40 to 85		32TSOP(I) Normal / 32SOP
			★LH28F020SUHT/N-L15	150	Vpp = 5 V					
4M	512k x 8	16k	LH28F004SUT-LF12	120	Vcc = 3.3 V (2.7 V read available)	35	80	0 to 70	40TSOP(I) Normal	
			LH28F004SUT-LF15	150	Vpp = 5 V					
			LH28F004SUHT-LF12	120	Vcc = 3.3 V (2.7 V read available)	35	80	-40 to 85		40TSOP(I) Normal
			LH28F004SUHT-LF15	150	Vpp = 5 V					
	512k x 8 256k x 16	16k	LH28F400SUE*/T/N*-LF12	120	Vcc = 3.3 V (2.7 V read available)	35	80	0 to 70	48TSOP(I) Normal*/ 56TSOP(I) Normal / 44SOP*	
			LH28F400SUE*/T/N*-LF15	150	Vpp = 5 V					
			LH28F400SUHE*/T/N*-LF12	120	Vcc = 3.3 V (2.7 V read available)	35	80	-40 to 85		48TSOP(I) Normal*/ 56TSOP(I) Normal / 44SOP*
			LH28F400SUHE*/T/N*-LF15	150	Vpp = 5 V					

### ■ Dual Work Flash Memory\*3

Capacity	Configuration (words x bits)	Erase block size (bytes)	Model No.	Access time (ns) MAX.	Supply voltage	Read current (mA) MAX. (f=10MHz)	Standby current ( $\mu$ A) MAX.	Operating temp. ( $^{\circ}$ C)	Package
4M	256k x 8 x 2	16k	LH28F040SUTD	150(190*2)	Vcc = 3.3 V (2.7 V read available) Vpp = 5 V	35	160	-20 to 70	40TSOP(I) Normal

\*1 Vcc = at 3.3 V \*2 Vcc = at 2.7 V

\*3 Dual work flash memory divides 4M-bit into two areas.  
Each area can read/write/erase independently.